

IN THE CLAIMS:

Please AMEND claim 27, as follows. For the Examiner's convenience, all claims currently pending in this application have been reproduced below:

1. (Previously Amended) A projection exposure apparatus, comprising:

a projection optical system for projecting a pattern of a first object onto a second object;

a first illumination system for illuminating the pattern of the first object under a first illumination condition, wherein the pattern of the first object illuminated under the first illumination condition is projected onto the second object through said projection optical system;

a second illumination system for performing illumination under a second illumination condition;

a light intensity detector, wherein an image of the pattern of the first object, as the same is illuminated by said second illumination system and under the second illumination condition, is formed through said projection optical system, and wherein said light intensity detector detects a light intensity distribution of the image; and

an information processing system for measuring a wavefront aberration of said projection optical system on the basis of the detection by said light intensity detector;

wherein the first illumination condition concerns spatially partial coherency or incoherency, and wherein said second illumination condition concerns spatially coherency or approximate coherency.

2. (Previously Amended) An apparatus according to Claim 1, wherein said information processing system is arranged to detect a phase distribution of the image of the pattern on the basis of light intensity distributions defined in relation to that image at different positions along an optical axis direction of said projection optical system, and to measure the wavefront aberration of said projection optical system on the basis of the detected phase distribution.

3. (Original) An apparatus according to Claim 1, wherein the second object is a photosensitive substrate, and wherein said projection optical system is used to project and print the transfer pattern, being illuminated under the first illumination condition, onto an exposure region on the photosensitive substrate.

4. (Previously Amended) An apparatus according to Claim 1, wherein said information processing system is arranged to measure the wavefront aberration of said projection optical system on the basis of light intensity distributions detected with respect to an imaging position of the image of the pattern and at least one defocus position of thereof, or of light intensity distributions with respect to different positions.

5. (Original) An apparatus according to Claim 4, wherein said information processing system measures the wavefront aberration of said projection optical system in accordance with a phase restoration method.

6. (Original) An apparatus according to Claim 4, wherein said first and second illumination systems include a common element.

7. (Previously Cancelled)

8. (Previously Cancelled)

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~~9.~~ (Previously Amended) An apparatus according to Claim 1, wherein, in each of said first and second illumination systems, a ratio of a numerical aperture of said first or second illumination system to a numerical aperture of said projection optical system is σ , and wherein the first illumination condition satisfies a relation $0.2 < \sigma \leq 1.0$ while the second illumination condition satisfies a relation $\sigma \leq 0.2$.

~~10.~~ (Previously) An apparatus according to Claim 1, wherein said first and second illumination systems include a common element.

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~~11.~~ (Previously Amended) A projection exposure apparatus, comprising:
a projection optical system for projecting a pattern of a first object onto a second object;
a first illumination system for illuminating the pattern of the first object under a first illumination condition, wherein the pattern of the first object illuminated under the first

illumination condition is projected onto the second object through said projection optical system;

a second illumination system for performing illumination under a second illumination condition;

a light intensity detector, wherein an image of the pattern of the first object, as the same is illuminated by said second illumination system and under the second illumination condition, is formed through said projection optical system, and wherein said light intensity detector detects a light intensity distribution of the image; and

an information processing system for measuring a wavefront aberration of said projection optical system on the basis of the detection by said light intensity detector;

wherein said first and second illumination systems include a common component, and wherein the first and second illumination conditions are defined exchangeably by adding a separate component to said common component or by removing said separate component.

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~~12~~. (Original) An apparatus according to Claim ⁸~~10~~, wherein interchanging the first and second illumination conditions with each other is performed by changing a light source to said common element.

¹⁰
~~13~~. (Original) An apparatus according to Claim 1, wherein said first and second illumination systems use different optical systems.

14-17. (Previously Cancelled)

¹¹
~~18.~~ (Original) An apparatus according to Claim ¹⁰~~13~~, wherein said first and second illumination systems use different light sources.

¹²
~~19.~~ (Original) An apparatus according to Claim 1, wherein said light intensity detector measures a light intensity distribution in accordance with a knife edge method.

¹³
~~20.~~ (Original) An apparatus according to Claim 1, further comprising an enlarging optical system for enlarging a light intensity distribution to be incident on said light intensity detector.

¹⁴
~~21.~~ (Original) An apparatus according to Claim 1, further comprising an adjusting mechanism for adjusting an aberration of said projection optical system on the basis of wavefront aberration information detected by said information processing system.

¹⁵
~~22.~~ (Original) An apparatus according to Claim 1, further comprising means for adjusting an aberration of said projection optical system, prior to projection of the transfer pattern onto the second object through said projection optical system, on the basis of wavefront aberration information detected by said information processing system and information related to the transfer pattern.

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~~23.~~ (Original) An apparatus according to Claim 1, wherein said second illumination system is usable for alignment between the first and second objects.

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~~24.~~ (Previously Amended) A device manufacturing method, comprising the steps of:
performing a projection exposure process for exposing a wafer to a pattern of a reticle, by use of a projection exposure apparatus which includes (i) a projection optical system for projecting a pattern of a first object onto a second object, (ii) a first illumination system for illuminating the pattern of the first object under a first illumination condition, wherein the pattern of the first object illuminated under the first illumination condition is projected onto the second object through said projection optical system, (iii) a second illumination system for performing illumination under a second illumination condition, (iv) a light intensity detector, wherein an image of the pattern of the first object, as the same is illuminated by said second illumination system and under the second illumination condition, is formed through said projection optical system, and wherein said light intensity detector detects a light intensity distribution of the image, and (v) an information processing system for measuring a wavefront aberration of said projection optical system on the basis of the detection by said light intensity detector, wherein said first and second illumination systems include a common component, and wherein the first and second illumination conditions are defined exchangeably by adding a separate component to said common component or by removing said separate component; and
developing the exposed wafer.

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~~25~~. (Original) A method according to Claim ¹⁸~~24~~, further comprising an adjusting step for adjusting an aberration of the projection optical system on the basis of the detected wavefront aberration.

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~~26~~. (Previously Added) A device manufacturing method, comprising the steps of:
transferring, by projection exposure, a pattern of a reticle onto a wafer with use of an exposure apparatus according to Claim 1; and
developing the exposed wafer.

²¹
~~27~~. (Currently Amended) A projection exposure apparatus, comprising:
an illumination optical system for illuminating a first object and being arranged to provide illumination under a first illumination condition and illumination under a second illumination condition, wherein the first illumination condition includes a first spatial coherency and the second illumination condition includes a second spatial coherency being different from the first spatial coherency;

a projection optical system for projecting a transfer pattern of a first object, as illuminated under the first illumination condition, onto a second object;

a first illumination system for illuminating the first object under a first illumination condition, wherein the transfer pattern of the first object illuminated under the first illumination condition is projected onto the second object through said projection optical system;

a second illumination system for providing illumination according to a second

illumination condition;

a light intensity detector for detecting a light intensity distribution of an image of a measurement pattern illuminated by said second illumination optical system under the second illumination condition, the image being formed through said projection optical system; and

an information processing system operable to measure wavefront aberration of said projection optical system on the basis of a result of a detection by said light intensity detector; detector.

wherein the first and second illumination conditions have different spatial coherencies.

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28. (Previously Added) A device manufacturing method, comprising the steps of:

transferring, by projection exposure, a pattern of a reticle onto a wafer with use of a projection exposure apparatus according to Claim 21; and
developing the exposed wafer.

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29. (Previously Added) An apparatus according to Claim 21, wherein the spatial coherency of the second illumination condition is higher than that of the first illumination condition.

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30. (Previously Added) An apparatus according to Claim 21, further comprising a first light source to be used in the first illumination condition and a second light source to be used in

the second illumination condition, wherein the first and second light sources differ from each other.

²⁵
~~31~~. (Previously Added) An apparatus according to Claim ²¹~~31~~, wherein said light intensity detector is disposed adjacent an imaging position of the measurement pattern being illuminated under the second illumination condition, wherein said light intensity detector is arranged to detect light intensity distributions at a different positions, being different from each other, and wherein said information processing system is arranged to measure the wavefront aberration of said projection optical system on the basis of the light intensity distributions measured at the different positions.

²⁶
~~32~~. (Previously Added) An apparatus according to Claim ²⁵~~31~~, wherein one of the different positions substantially corresponds to the imaging position of the measurement pattern.

²⁷
~~33~~. (Previously Added) An apparatus according to Claim ²¹~~31~~, wherein the transfer pattern and the measurement pattern differ from each other.

²⁸
~~34~~. (Previously Added) An exposure apparatus, comprising:
an illumination optical system for illuminating a first object and being arranged to provide illumination under a first illumination condition and illumination under a second illumination condition, wherein the first illumination condition includes a first spatial coherency

and the second illumination condition includes a second spatial coherency being different from the first spatial coherency;

a projection optical system for projecting a transfer pattern, as illuminated under the first illumination condition, onto a second object;

a light intensity detector for detecting light intensity distributions at different detection positions, being different from each other, with respect to an imaging position of a measurement pattern as illuminated under the second illumination condition, the imaging position being defined by said projection optical system; and

an information processing system for measuring wavefront aberration of said projection optical system on the basis of a result of detection of the light intensity distributions at the different detection positions made through said light intensity detector.

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~~35~~. (Previously Added) An apparatus according to Claim *28* ~~34~~, wherein the second spatial coherency under the second illumination condition is higher than the first spatial coherency under the first illumination condition.

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~~36~~. (Previously Added) An apparatus according to Claim *28* ~~34~~, further comprising an adjusting unit for adjusting a size of an effective light source of said illumination optical system, as the first and second illumination conditions are to be switched from one to the other.

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~~37~~. (Previously Added) An apparatus according to Claim ²⁸~~34~~, wherein said illumination optical system includes a stop member, and wherein said stop member is adjusted as the first and second illumination conditions are to be switched from one to the other.

³²
~~38~~. (Previously Added) An apparatus according to Claim ³¹~~37~~, wherein an aperture defined under the first illumination condition is larger than an aperture defined under the second illumination condition.

³³
~~39~~. (Previously Added) An apparatus according to Claim ²⁸~~34~~, further comprising a coherency-transforming optical system which is arranged to be inserted into and/or demounted from said illumination optical system as the first and second illumination conditions are to be switched from one to the other.

³⁴
~~40~~. (Previously Added) An apparatus according to Claim ²⁸~~34~~, further comprising a first light source to be used in the first illumination condition and a second light source to be used in the second illumination condition, wherein the first and second light sources differ from each other.

³⁵
~~41~~. (Previously Added) An apparatus according to Claim ²⁸~~34~~, wherein the transfer pattern and the measurement pattern differ from each other.

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~~42~~. (Previously Added) An apparatus according to Claim ²⁸~~34~~, wherein the transfer pattern and the measurement pattern differ from each other.

³⁷
~~43~~. (Previously Added) A device manufacturing method, comprising:
a projection exposure step for transferring, by projection exposure, a pattern of a reticle onto a wafer by use of an exposure apparatus as recited in Claim ²⁸~~34~~; and
a development step for developing the wafer processed by said projection exposure step.

³⁸
~~44~~. (Previously Added) An exposure apparatus, comprising:
an illumination optical system for illuminating a first object and being arranged to provide illumination under a first illumination condition and illumination under a second illumination condition, wherein the first illumination condition includes a first spatial coherency and the second illumination condition includes a second spatial coherency being different from the first spatial coherency;
a projection optical system for projecting a transfer pattern, as illuminated under the first illumination condition, onto a second object;
a light intensity detector for detecting an intensity distribution of light directed by said projection optical system to said light intensity detector, from a measurement pattern being illuminated under the second illumination condition;
an information processing system for measuring wavefront aberration of said

projection optical system on the basis of a result of detection by said light intensity detector; and
an adjusting unit for adjusting a size of an effective light source of said
illumination optical system as the first and second illumination conditions are to be switched
from one to the other.

³⁹
~~45~~. (Previously Added) An apparatus according to Claim ~~44~~³⁸, wherein the second spatial
coherency under the second illumination condition is higher than the first spatial coherency under
the first illumination condition.

⁴⁰
~~46~~. (Previously Added) An apparatus according to Claim ~~44~~³⁸, wherein said adjusting unit
includes a stop member having an aperture, and wherein the aperture of said stop member is
adjusted as the first and second illumination conditions are to be switched from one to the other.

⁴¹
~~47~~. (Previously Added) An apparatus according to Claim ~~46~~⁴⁰, wherein the aperture
defined under the first illumination condition is larger than the aperture defined under the second
illumination condition.

⁴²
~~48~~. (Previously Added) An apparatus according to Claim ~~44~~³⁸, further comprising a
coherency-transforming optical system which is arranged to be inserted into and/or demounted
from said illumination optical system as the first and second illumination conditions are to be
switched from one to the other.

⁴³
~~43~~. (Previously Added) An apparatus according to Claim 44, further comprising a first light source to be used in the first illumination condition and a second light source to be used in the second illumination condition, wherein the first and second light sources differs from each other.

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~~50~~. (Previously Added) An apparatus according to Claim ~~44~~³⁸, wherein said light intensity detector is arranged to detect light intensity distributions at different detection positions, being different from each other, with respect to an imaging position of a measurement pattern as illuminated under the second illumination condition, the imaging position being defined by said projection optical system, and wherein said information processing system is arranged to measure the wavefront aberration of said projection optical system on the basis of a result of detection of the light intensity distributions at the different detection positions made through said light intensity detector.

⁴⁵
~~51~~. (Previously Added) An apparatus according to Claim ~~44~~³⁸, wherein one of the different detection positions substantially corresponds to the imaging position of the measurement pattern.

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~~52~~. (Previously Added) An apparatus according to Claim ~~44~~³⁸, wherein the transfer pattern and the measurement pattern differ from each other.

⁴⁷
~~53.~~ (Previously Added) A device manufacturing method, comprising:

a projection exposure step for transferring, by projection exposure, a pattern of a reticle onto a wafer by use of an exposure apparatus as recited in Claim ~~44~~⁴³, and
a development step for developing the wafer processed by said projection exposure step.

⁴⁸
~~54.~~ (Previously Added) An exposure apparatus, comprising:

an illumination optical system for illuminating a first object and being arranged to provide illumination under a first illumination condition and illumination under a second illumination condition, wherein said first illumination condition includes a first spatial coherency and said second illumination condition includes a second spatial coherency being different from the first spatial coherency;

a projection optical system for projection a transfer pattern, as illuminated under the first illumination condition, onto a second object;

a light intensity detector for detecting an intensity distribution of light directed by said projection optical system to said light intensity detector, from a measurement pattern being illuminated under the second illumination condition; and

an information processing system for measuring wavefront aberration of said projection optical system on the basis of a result of detection by said light intensity detector;

wherein said illumination optical system includes a coherency-transforming optical system which is arranged to be inserted into and/or demounted from said illumination

optical system as the first and second illumination conditions are to be switched from one to the other.

⁴⁹
~~55.~~ (Previously Added) An apparatus according to Claim ~~54~~⁴⁸, wherein the second spatial coherency under the second illumination condition is higher than the first spatial coherency under the first illumination condition.

⁵⁰
~~56.~~ (Previously Added) An apparatus according to Claim ~~54~~⁴⁸, further comprising an adjusting unit for adjusting a size of an effective light source of said illumination optical system as the first and second illumination conditions are to be switched from one to the other.

⁵¹
~~57.~~ (Previously Added) An apparatus according to Claim ~~56~~⁵⁰, wherein said adjusting unit includes a stop member having an aperture, and wherein the aperture of said stop member is adjusted as the first and second illumination conditions are to be switched from one to the other.

⁵²
~~58.~~ (Previously Added) An apparatus according to Claim ~~57~~⁵¹, wherein the aperture defined under the first illumination condition is larger than the aperture defined under the second illumination condition.

⁵³
~~59.~~ (Previously Added) An apparatus according to Claim ~~54~~⁴⁸, wherein said light intensity detector is arranged to detect light intensity distributions at different detection positions, being

different from each other, with respect to an imaging position of a measurement pattern as illuminated under the second illumination condition, the imaging position being defined by said projection optical system, and wherein said information processing system is arranged to measure the wavefront aberration of said projection optical system on the basis of a result of detection of the light intensity distributions at the different detection positions made through said light intensity detector.

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60. (Previously Added) An apparatus according to Claim *53*, wherein one of the different detection positions substantially corresponds to the imaging position of the measurement pattern.

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61. (Previously Added) An apparatus according to Claim *54*, wherein the transfer pattern and the measurement pattern differ from each other.

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62. (Previously Added) A device manufacturing method, comprising:
a projection exposure step for transferring, by projection exposure, a pattern of a reticle onto a wafer by use of an exposure apparatus as recited in Claim *54*; and
a development step for developing the wafer processed by said projection exposure step.